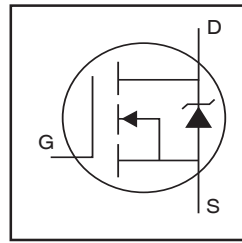


AUIRF1324WL

WIDELEAD HEXFET® Power MOSFET

Features

- Advanced Process Technology
- Ultra Low On-Resistance
- 50% Lower Lead Resistance
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to T_{jmax}
- Lead-Free, RoHS Compliant
- Automotive Qualified *



| | | |
|-------------------------|------|---------------|
| $V_{(BR)DSS}$ | | 24V |
| $R_{DS(on)}$ | typ. | 1.16mΩ |
| | max. | 1.30mΩ |
| I_D (Silicon Limited) | | 382A ① |
| I_D (Package Limited) | | 240A |

Description

Specifically design for automotive applications this Widelead TO-262 package part has the advantage of having over 50% lower lead resistance and delivering over 20% lower $R_{ds(on)}$ when compared with a traditional TO-262 package housing the same silicon die. This greatly helps in reducing condition losses, achieving higher current levels or enabling a system to run cooler and have improved efficiency. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive and other applications.



| | | |
|----------|----------|----------|
| G | D | S |
| Gate | Drain | Source |

Absolute Maximum Ratings

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

| | Parameter | Max. | Units |
|------------------------------|--|----------------------------|-------|
| $I_D @ T_C = 25^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ (Silicon Limited) | 382① | A |
| $I_D @ T_C = 100^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ (Silicon Limited) | 270① | |
| $I_D @ T_C = 25^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ (Package Limited) | 240 | |
| I_{DM} | Pulsed Drain Current ② | 1530 | |
| $P_D @ T_C = 25^\circ C$ | Maximum Power Dissipation | 300 | W |
| | Linear Derating Factor | 2.0 | W/°C |
| V_{GS} | Gate-to-Source Voltage | ± 20 | V |
| E_{AS} (Thermally limited) | Single Pulse Avalanche Energy ③ | 530 | mJ |
| I_{AR} | Avalanche Current ② | See Fig. 14, 15, 22a, 22b, | A |
| E_{AR} | Repetitive Avalanche Energy ② | | mJ |
| dv/dt | Peak Diode Recovery ④ | 1.3 | V/ns |
| T_J T_{STG} | Operating Junction and Storage Temperature Range | -55 to + 175 | °C |
| | Soldering Temperature, for 10 seconds | 300 (1.6mm from case) | |

Thermal Resistance

| | Parameter | Typ. | Max. | Units |
|-----------------|--------------------|------|------|-------|
| $R_{\theta JC}$ | Junction-to-Case ⑧ | — | 0.50 | °C/W |

HEXFET® is a registered trademark of International Rectifier.

*Qualification standards can be found at <http://www.irf.com/>

Static Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|--|--------------------------------------|------|-------|------|-------|---|
| V _{(BR)DSS} | Drain-to-Source Breakdown Voltage | 24 | — | — | V | V _{GS} = 0V, I _D = 250μA |
| ΔV _{(BR)DSS} /ΔT _J | Breakdown Voltage Temp. Coefficient | — | 0.022 | — | V/°C | Reference to 25°C, I _D = 5mA ⑤ |
| R _{DS(on)} | Static Drain-to-Source On-Resistance | — | 1.16 | 1.30 | mΩ | V _{GS} = 10V, I _D = 195A ⑤ |
| V _{GS(th)} | Gate Threshold Voltage | 2.0 | — | 4.0 | V | V _{DS} = V _{GS} , I _D = 250μA |
| g _{fs} | Forward Transconductance | 210 | — | — | S | V _{DS} = 10V, I _D = 195A |
| R _G | Internal Gate Resistance | — | 2.4 | — | Ω | |
| I _{DSS} | Drain-to-Source Leakage Current | — | — | 20 | μA | V _{DS} = 24V, V _{GS} = 0V |
| | | — | — | 250 | | V _{DS} = 19V, V _{GS} = 0V, T _J = 125°C |
| I _{GSS} | Gate-to-Source Forward Leakage | — | — | 200 | nA | V _{GS} = 20V |
| | Gate-to-Source Reverse Leakage | — | — | -200 | | V _{GS} = -20V |

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|----------------------------|---|------|------|------|-------|--|
| Q _g | Total Gate Charge | — | 120 | 180 | nC | I _D = 195A |
| Q _{gs} | Gate-to-Source Charge | — | 58 | — | | V _{DS} = 12V |
| Q _{gd} | Gate-to-Drain ("Miller") Charge | — | 36 | — | | V _{GS} = 10V ⑤ |
| Q _{sync} | Total Gate Charge Sync. (Q _g - Q _{gd}) | — | 84 | — | | I _D = 195A, V _{DS} = 0V, V _{GS} = 10V ⑤ |
| t _{d(on)} | Turn-On Delay Time | — | 18 | — | ns | V _{DD} = 16V |
| t _r | Rise Time | — | 200 | — | | I _D = 195A |
| t _{d(off)} | Turn-Off Delay Time | — | 75 | — | | R _G = 2.7Ω |
| t _f | Fall Time | — | 110 | — | | V _{GS} = 10V ⑤ |
| C _{iss} | Input Capacitance | — | 7630 | — | pF | V _{GS} = 0V |
| C _{oss} | Output Capacitance | — | 3390 | — | | V _{DS} = 19V |
| C _{rss} | Reverse Transfer Capacitance | — | 1960 | — | | f = 1.0MHz, See Fig.5 |
| C _{oss} eff. (ER) | Effective Output Capacitance (Energy Related) | — | 4660 | — | | V _{GS} = 0V, V _{DS} = 0V to 19V ⑦, See Fig.11 |
| C _{oss} eff. (TR) | Effective Output Capacitance (Time Related) | — | 4685 | — | | V _{GS} = 0V, V _{DS} = 0V to 19V ⑥ |

Diode Characteristics

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|------------------|--|--|------|------|-------|--|
| I _S | Continuous Source Current (Body Diode) | — | — | 382① | A | MOSFET symbol showing the integral reverse p-n junction diode. |
| I _{SM} | Pulsed Source Current (Body Diode) ② | — | — | 1530 | | |
| V _{SD} | Diode Forward Voltage | — | — | 1.3 | V | T _J = 25°C, I _S = 195A, V _{GS} = 0V ③ |
| t _{rr} | Reverse Recovery Time | — | 46 | 69 | ns | T _J = 25°C V _R = 20V, |
| | | — | 45 | 68 | | T _J = 125°C I _F = 195A |
| Q _{rr} | Reverse Recovery Charge | — | 395 | 593 | nC | T _J = 25°C di/dt = 100A/μs ⑤ |
| | | — | 345 | 518 | | T _J = 125°C |
| I _{RRM} | Reverse Recovery Current | — | 1.9 | — | A | T _J = 25°C |
| t _{on} | Forward Turn-On Time | Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD) | | | | |

Notes:

- ① Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 240A. Note that current limitations arising from heating of the device leads may occur with some lead mounting arrangements.(Refer to AN-1140 <http://www.irf.com/technical-info/appnotes/an-1140.pdf>)
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ Limited by T_{Jmax}, starting T_J = 25°C, L = 0.028mH
R_G = 50Ω, I_{AS} = 195A, V_{GS} = 10V. Part not recommended for use above this value.
- ④ I_{SD} ≤ 195A, di/dt ≤ 600A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 175°C.
- ⑤ Pulse width ≤ 400μs; duty cycle ≤ 2%.
- ⑥ C_{oss} eff. (TR) is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.
- ⑦ C_{oss} eff. (ER) is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.
- ⑧ R_θ is measured at T_J approximately 90°C.

Qualification Information[†]

| | | | |
|-----------------------------------|----------------------|---|------|
| Qualification Level | | Automotive (per AEC-Q101) ^{††} | |
| | | Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level. | |
| Moisture Sensitivity Level | | TO-262 WideLead | MSL1 |
| ESD | Machine Model | Class M4 (+/- 425V) ^{†††} AEC-Q101-002 | |
| | Human Body Model | Class H2 (+/- 4000V) ^{†††} AEC-Q101-001 | |
| | Charged Device Model | Class C5 (+/- 1125V) ^{†††} AEC-Q101-005 | |
| RoHS Compliant | | Yes | |

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/>

†† Exceptions (if any) to AEC-Q101 requirements are noted in the qualification report.

††† Highest passing voltage.

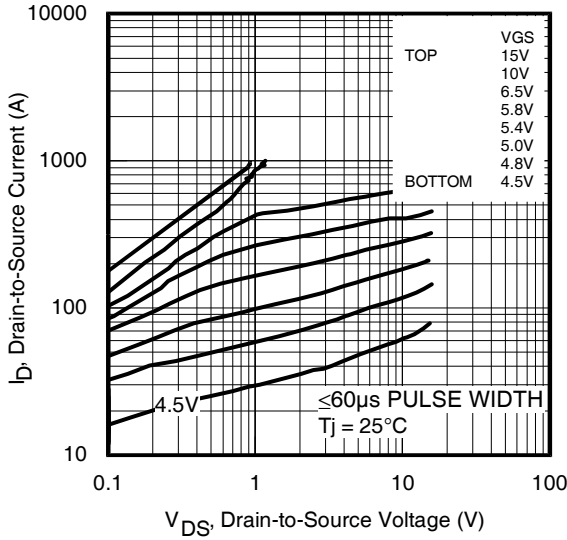


Fig 1. Typical Output Characteristics

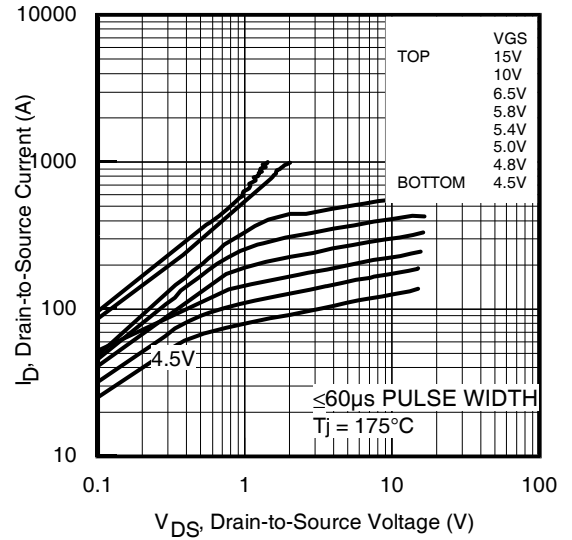


Fig 2. Typical Output Characteristics

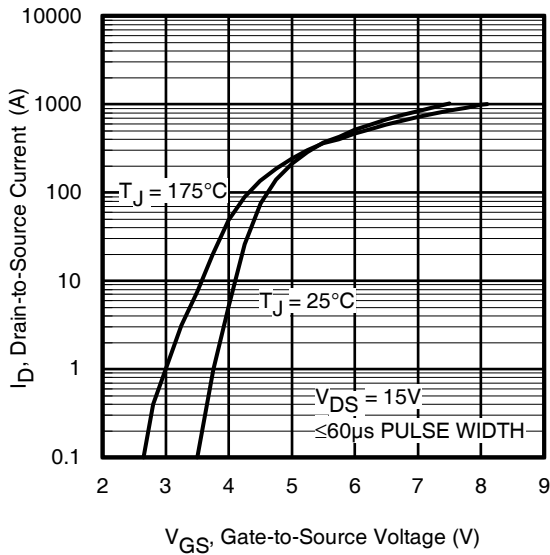


Fig 3. Typical Transfer Characteristics

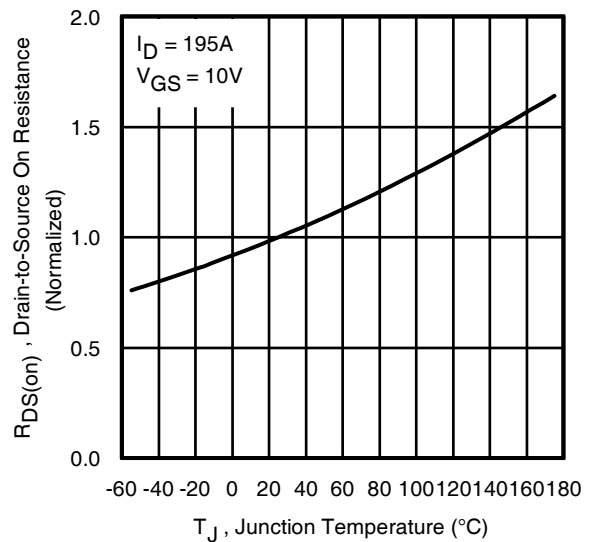


Fig 4. Normalized On-Resistance vs. Temperature

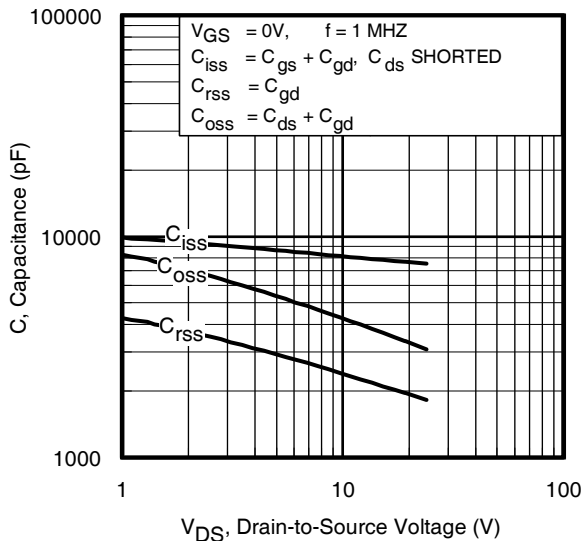


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

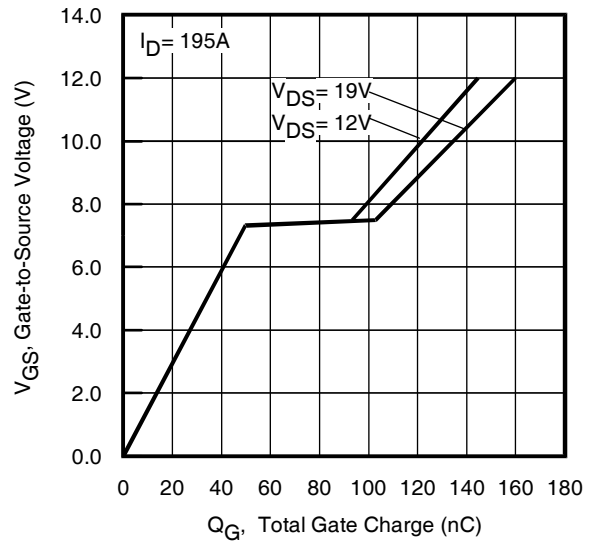


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

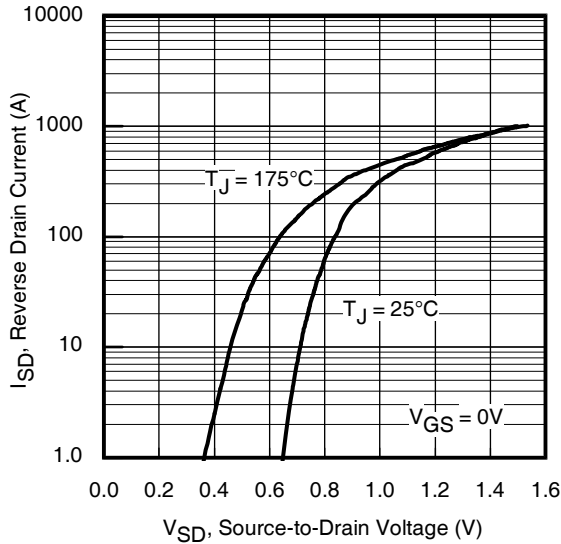


Fig 7. Typical Source-Drain Diode Forward Voltage

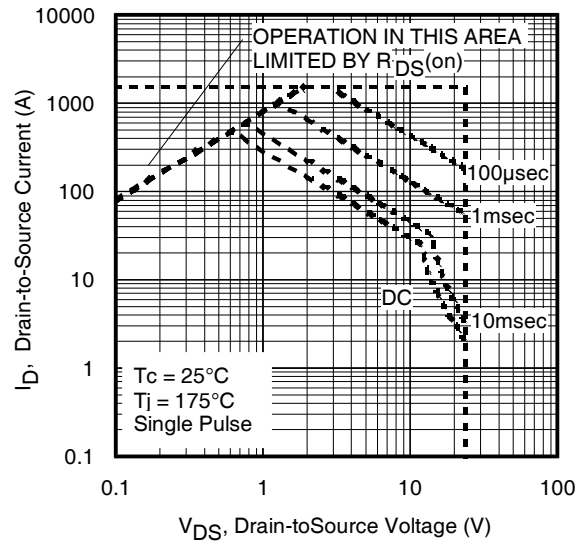


Fig 8. Maximum Safe Operating Area

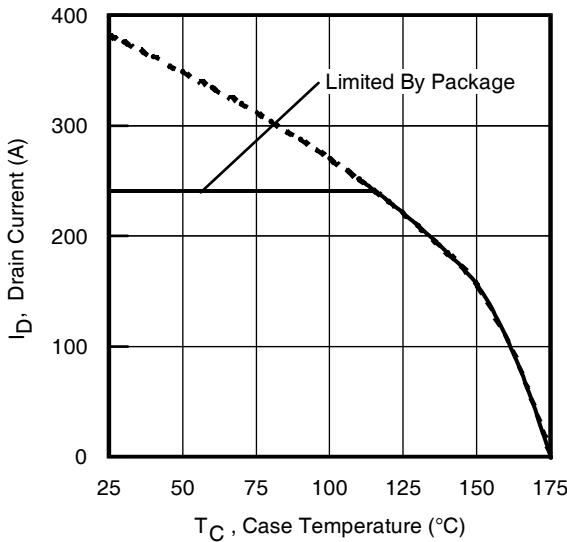


Fig 9. Maximum Drain Current vs. Case Temperature

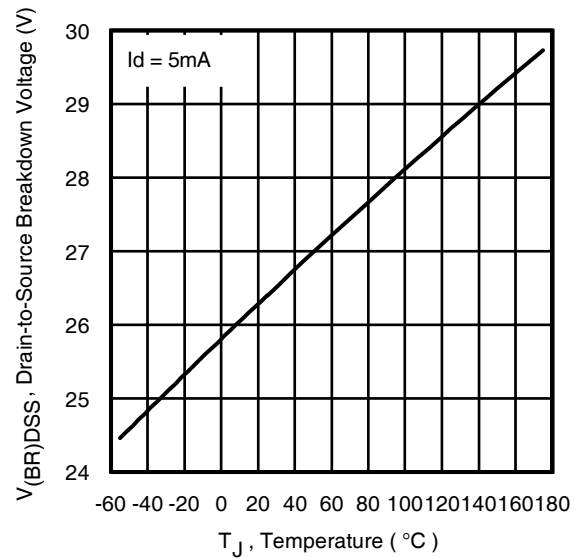


Fig 10. Drain-to-Source Breakdown Voltage

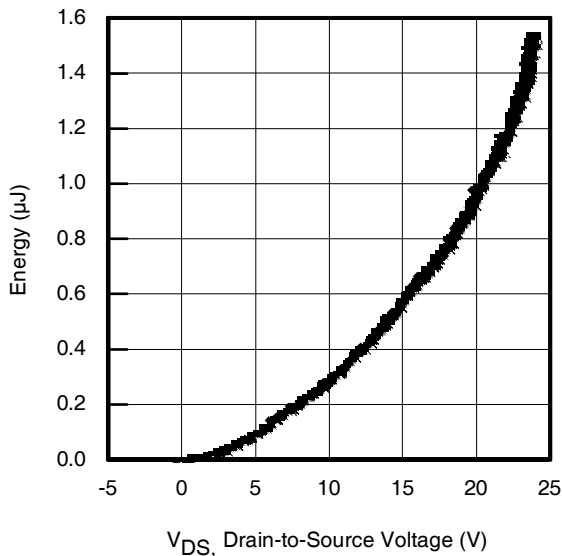


Fig 11. Typical C_{OSS} Stored Energy

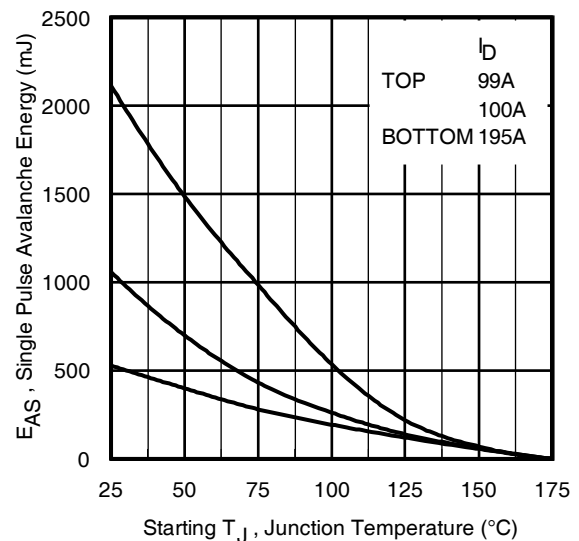


Fig 12. Maximum Avalanche Energy vs. Drain Current

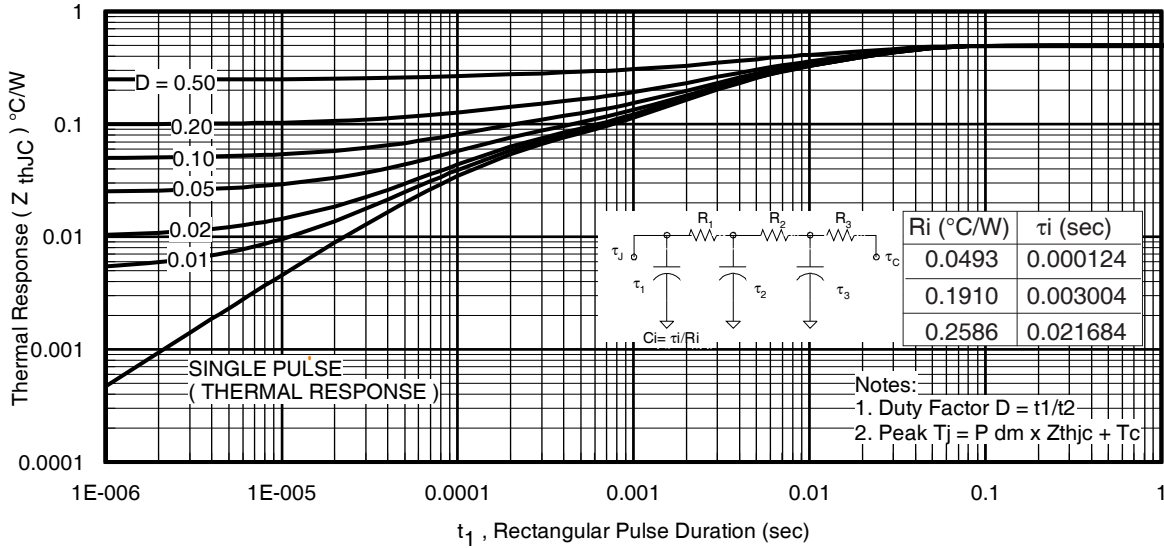


Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

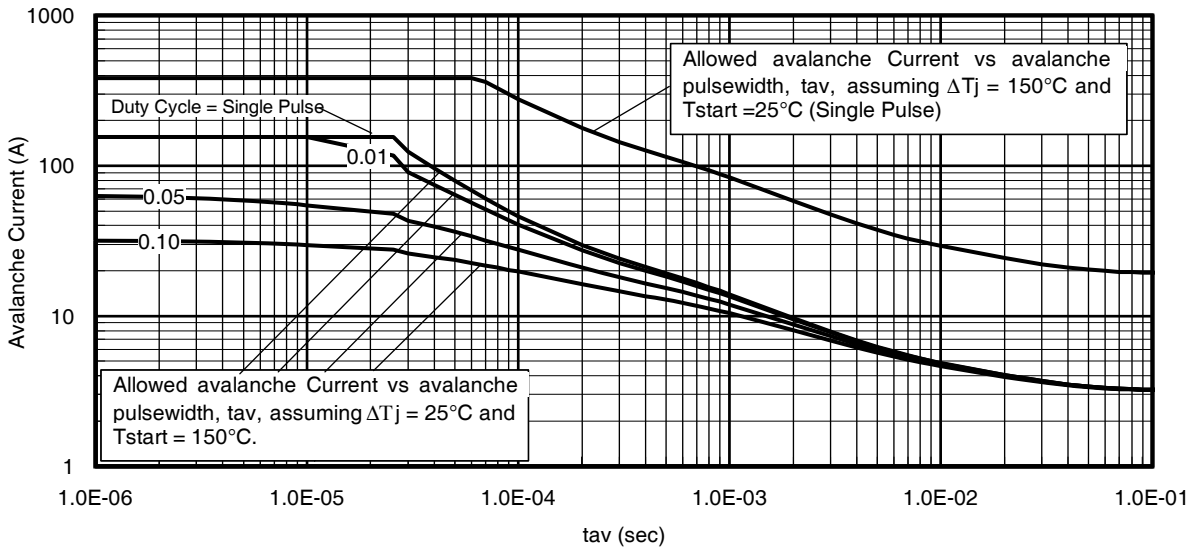
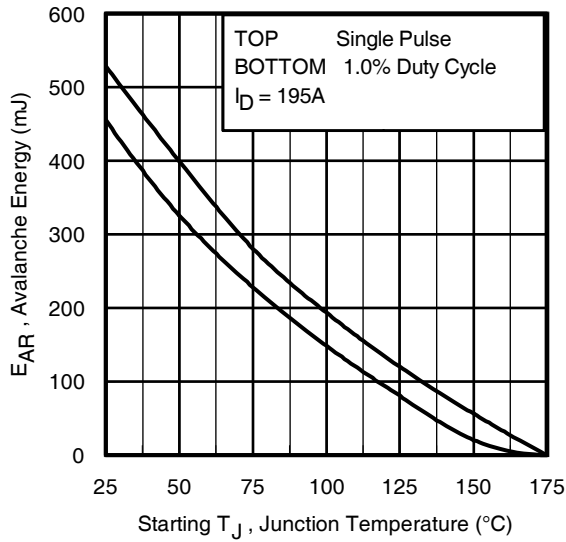


Fig 14. Typical Avalanche Current vs. Pulsewidth



**Notes on Repetitive Avalanche Curves , Figures 14, 15:
(For further info, see AN-1005 at www.irf.com)**

1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figure 22a, 22b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 14, 15).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13)

$$P_{D(ave)} = \frac{1}{2} (1.3 \cdot BV \cdot I_{av}) = \frac{\Delta T}{Z_{thJC}}$$

$$I_{av} = \frac{2\Delta T}{[1.3 \cdot BV \cdot Z_{th}]}$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

Fig 15. Maximum Avalanche Energy vs. Temperature

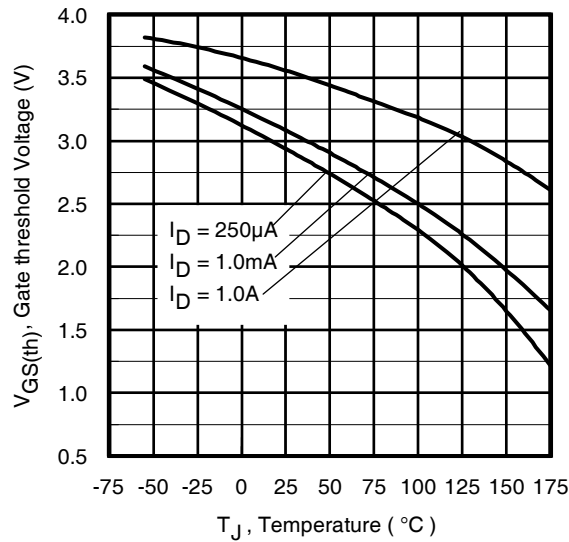
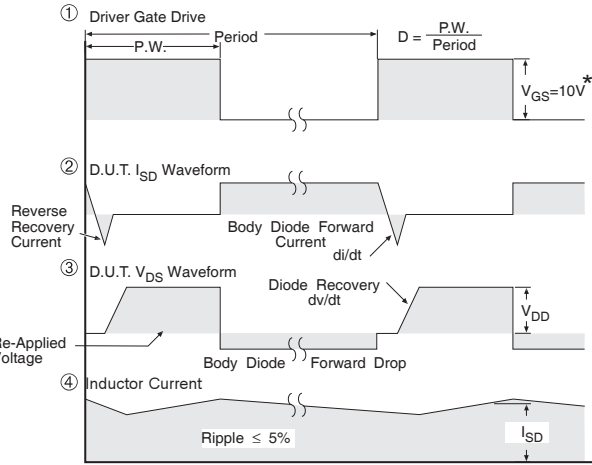
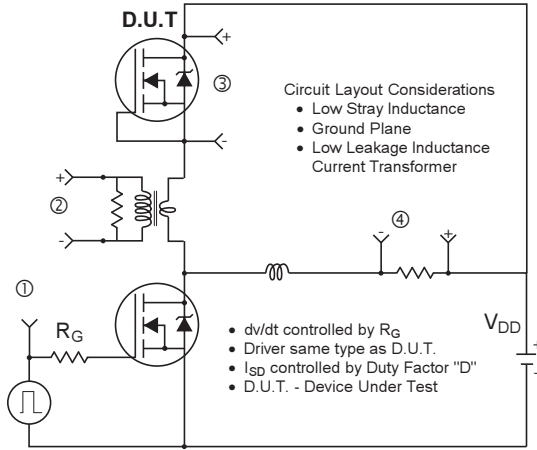


Fig 16. Threshold Voltage vs. Temperature



* $V_{GS} = 5V$ for Logic Level Devices

Fig 21. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

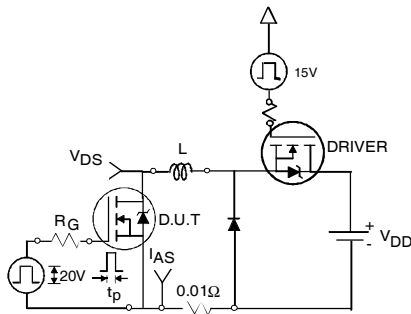


Fig 22a. Unclamped Inductive Test Circuit

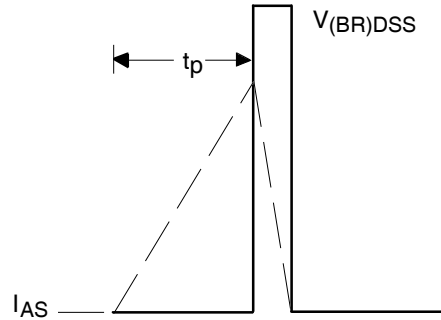


Fig 22b. Unclamped Inductive Waveforms

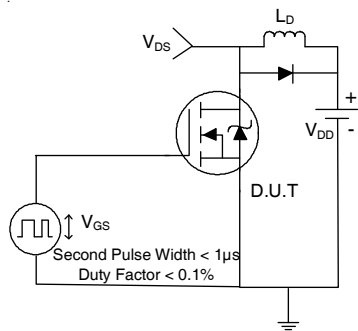


Fig 23a. Switching Time Test Circuit

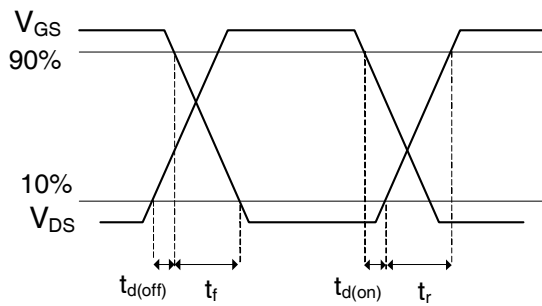


Fig 23b. Switching Time Waveforms

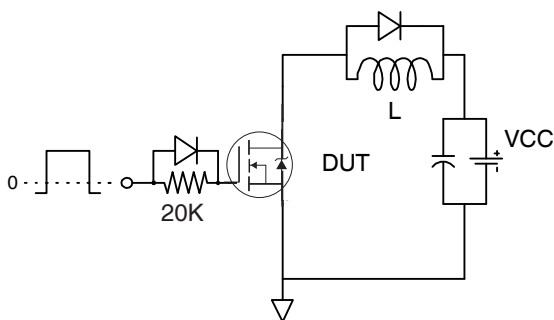


Fig 24a. Gate Charge Test Circuit

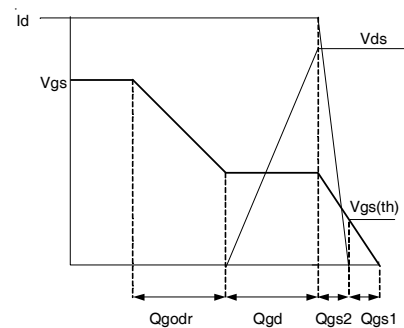
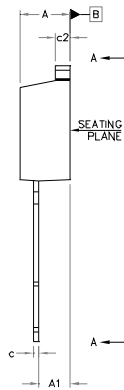
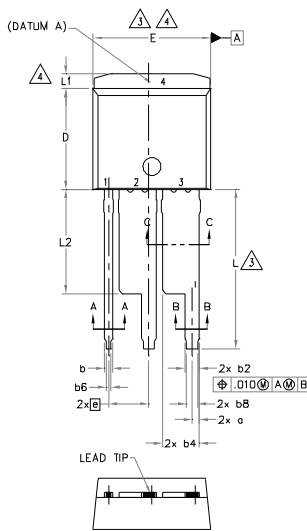


Fig 24b. Gate Charge Waveform

TO-262 WideLead Package Outline

Dimensions are shown in millimeters (inches)



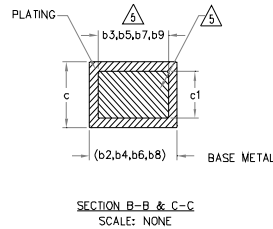
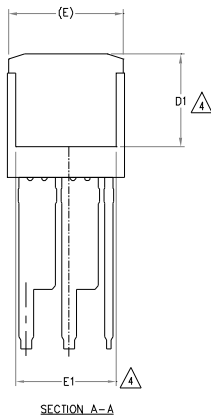
| SYMBOL | DIMENSIONS | | | | NOTES |
|--------|-------------|-------|----------|------|-------|
| | MILLIMETERS | | INCHES | | |
| | MIN. | MAX. | MIN. | MAX. | |
| A | 4.06 | 4.83 | .160 | .190 | 5 |
| A1 | 2.03 | 3.02 | .080 | .119 | |
| a | 0.20 | 0.51 | .008 | .020 | 5 |
| b | 0.51 | 0.91 | .020 | .036 | |
| b1 | 0.51 | 0.81 | .020 | .032 | 5 |
| b2 | 1.07 | 1.47 | 0.42 | .058 | |
| b3 | 1.07 | 1.37 | .042 | .054 | 5 |
| b4 | 3.05 | 3.45 | .120 | .136 | |
| b5 | 3.05 | 3.35 | .120 | .132 | 5 |
| b6 | 0.25 | 0.61 | .010 | .024 | |
| b7 | 0.25 | 0.51 | .010 | .020 | 5 |
| b8 | 0.76 | 1.17 | .030 | .046 | |
| b9 | 0.76 | 1.07 | .030 | .022 | 5 |
| c | 0.38 | 0.74 | .015 | .029 | |
| c1 | 0.38 | 0.58 | .015 | .023 | 5 |
| c2 | 1.14 | 1.65 | .045 | .065 | |
| D | 8.51 | 9.65 | .335 | .380 | 3 |
| D1 | 6.86 | 7.42 | .270 | .292 | |
| E | 9.65 | 10.67 | .380 | .420 | 3,4 |
| E1 | 6.22 | 8.48 | .245 | .334 | |
| e | 3.81 BSC | | .150 BSC | | 4 |
| L | 13.46 | 14.10 | .530 | .555 | |
| L1 | - | 1.65 | - | .065 | 4 |
| L2 | 8.64 | 9.40 | .340 | .370 | |

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
 2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
 3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
 4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
 5. DIMENSION b3, b5, b7, b9 AND c1 APPLY TO BASE METAL ONLY.
 6. CONTROLLING DIMENSION: INCH.
 - 7.- OUTLINE CONFORM TO JEDEC TO-262 EXCEPT A1(max.), b(min.) AND D1(min.) WHERE DIMENSIONS DERIVED THE ACTUAL PACKAGE OUTLINE.

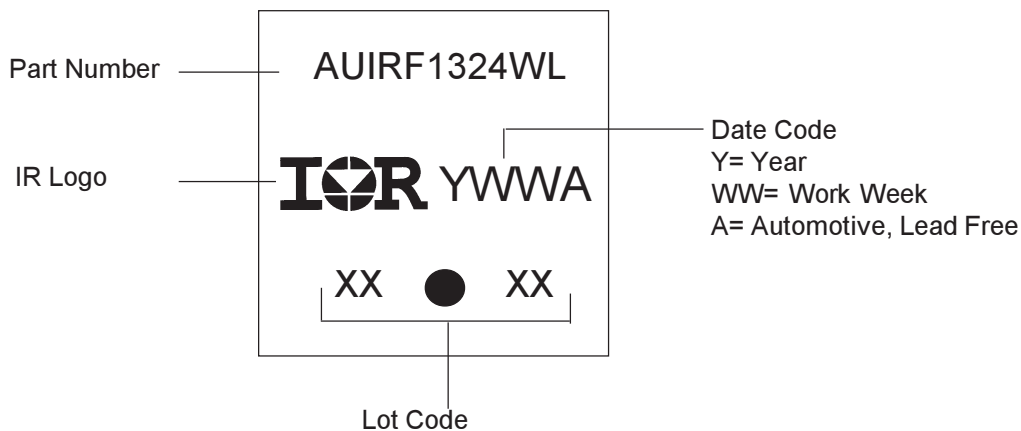
LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE



TO-262 WideLead Part Marking Information



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>
www.irf.com

Ordering Information

| Base part number | Package Type | Standard Pack | | Complete Part Number |
|------------------|-----------------|---------------|----------|----------------------|
| | | Form | Quantity | |
| AUIRF1324WL | TO-262 WideLead | Tube | 50 | AUIRF1324WL |

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For technical support, please contact IR’s Technical Assistance Center

<http://www.irf.com/technical-info/>

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Tel: (310) 252-7105